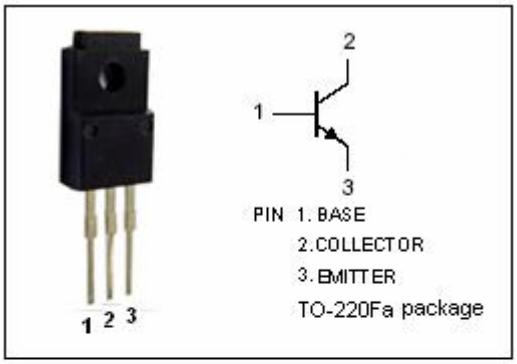
isc Silicon NPN Power Transistor — 2SD2151

DESCRIPTION

- Low Collector Saturation Voltage
  : $V_{CE(sat)}$= 0.5V(Max)@ I_C= 6A
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 80V (Min)
- Good Linearity of h_{FE}
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

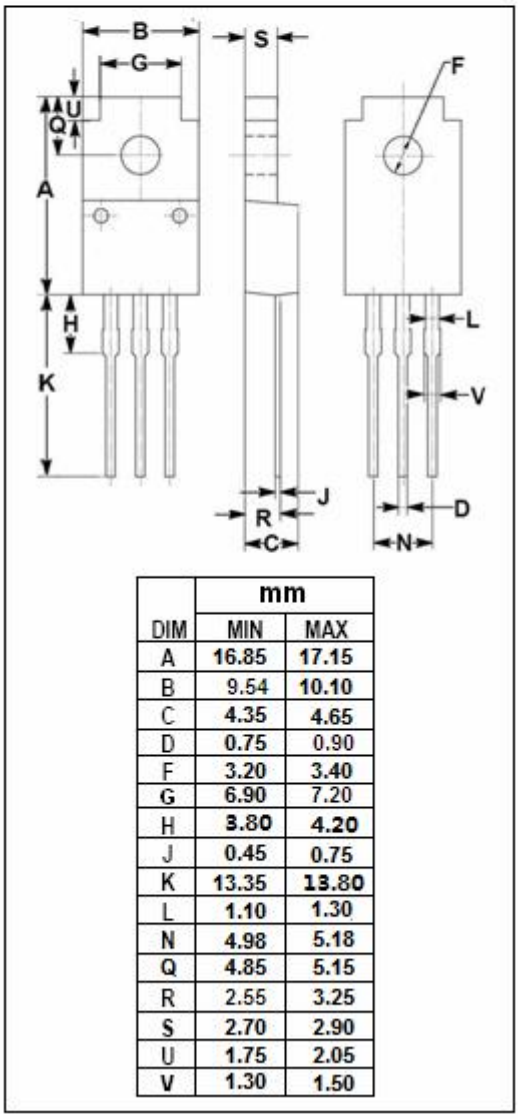


APPLICATIONS

- Designed for power switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	130	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	10	A
I_{CM}	Collector Current-Peak	20	A
P_C	Collector Power Dissipation @ T_C=25℃	30	W
	Collector Power Dissipation @ T_a=25℃	2	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	3.80	4.20
J	0.45	0.75
K	13.35	13.80
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	80			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 6A; I_B= 0.3A			0.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 10A; I_B= 1A			1.5	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= 6A; I_B= 0.3A			1.5	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= 10A; I_B= 1A			2.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 100V; I_E= 0			10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			50	μA
h_{FE-1}	DC Current Gain	I_C= 0.1A; V_{CE}= 2V	45			
h_{FE-2}	DC Current Gain	I_C= 3A; V_{CE}= 2V	90		260	
h_{FE-3}	DC Current Gain	I_C= 6A; V_{CE}= 2V	30			
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 10V; f= 10MHz		20		MHz

◆ **h_{FE-2} classifications**

Q	P
90-180	130-260